

TSMC 98-262
Serial Number 09/325,951



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AMENDMENT AND RESPONSE TO OFFICE ACTION

TO: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D. C. 20231

FROM: George O. Saile (Reg. No. 19,572)
20 McIntosh Drive
Poughkeepsie, NY 12603

DATE: 07 March 2002

REF: APPLICANT : Chiang et al.
SERIAL NO. : 09/325,951
ART UNIT : 2812
FILING DATE : 06/10/99
ATTY NO. : TSMC 98-262
EXAMINER : R. Pompey
TITLE : Method for Forming High Purity Silicon Oxide Field
Oxide Isolation Region

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TECHNICAL SERVICES 2800

Sir:

In response to an office action mailed on 02 October 2001, please consider the following amendments and remarks pertaining to the above referenced application.

03/27/2002 DTESSEM1 00000039 190033 09325951
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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class mail in an envelope addressed to the Commissioner of Patents and Trademarks, Washington, D. C. 20231 on 12 March 2002.

Stephen B. Ackerman
Name Reg # 37,761

SSB
Signature

3/12/02
Date